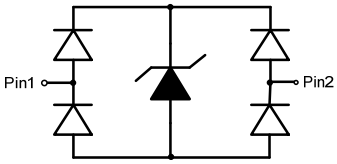
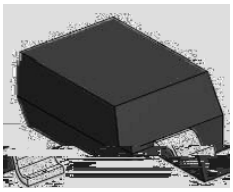
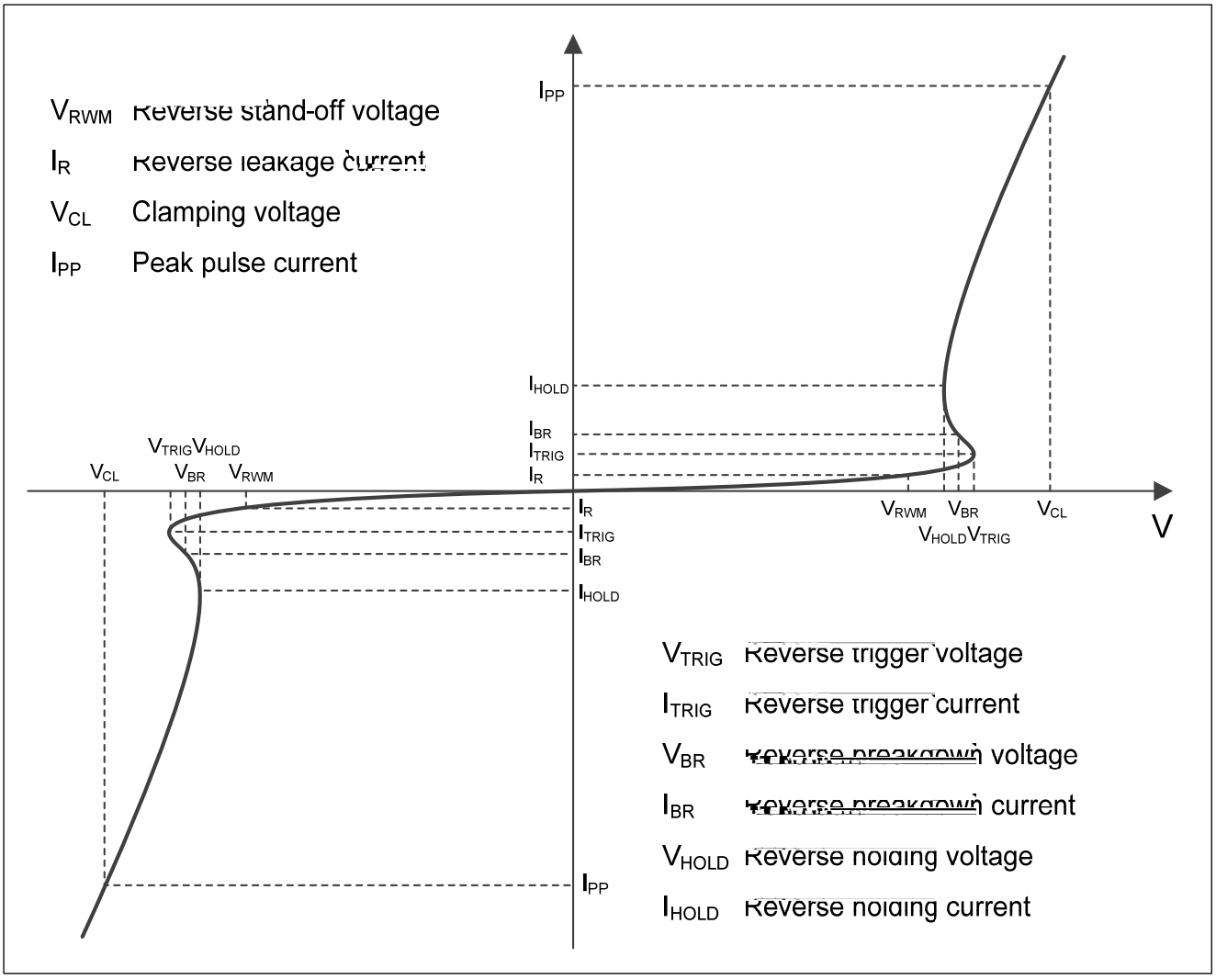




SOD-323

Stand-off voltage: 3.3V Max
Transient protection for each line according to IEC61000-4-2(ESD): ±30kV (contact)
IEC61000-4-5(surge): 7A (8/20 s)
Ultra-low capacitance: C_J = 1.35pF typ.
Low leakage current: I_R <1nA typ.
Low clamping voltage: V_{CL} = 12.0V typ. @ I_{PP} = 16A (TLP)
Solid-state silicon technology

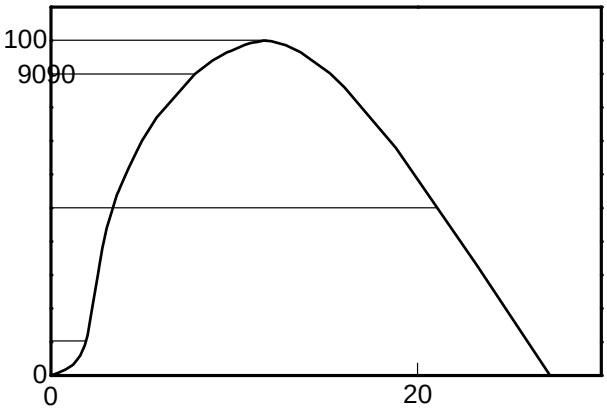
: SOD323
: Tin plated leads, solderable per



Peak pulse power (t_p = 8/20 s)	P_{pk}	77	W
Peak pulse current (t_p = 8/20 s)	I_{PP}	7	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	±30	KV
ESD according to IEC61000-4-2 contact discharge		±30	
Junction temperature	T_J	125	°C
Operating temperature	T_{OP}	-40~85	°C
Storage temperature	T_{STG}	-55~150	°C

Reverse maximum working voltage	V_{RWM}	V				3.3
Reverse leakage current	I_R	nA	V_{RWM} = 3.3V		<1	50
Reverse breakdown voltage	$V_{(BR)}$	V	I_{BR} = 1mA	6.0	8	
Clamping voltage [1]	V_{CL}	V	I_{PP} = 16A, t_p = 100ns		13	
Dynamic resistance [1]	R_{DYN}				0.55	
Clamping voltage [2]	V_{CL}	V	V_{ESD} = 8kV		13	
Clamping voltage [3]	V_{CL}	V	I_{PP} = 1A, t_p = 8/20 s		8.1	9
			I_{PP} = 7A, t_p = 8/20 s		9.7	11
Junction capacitance	C_J	pF	V_R = 0V, f = 1MHz		0.8	1.0

μ - - - -



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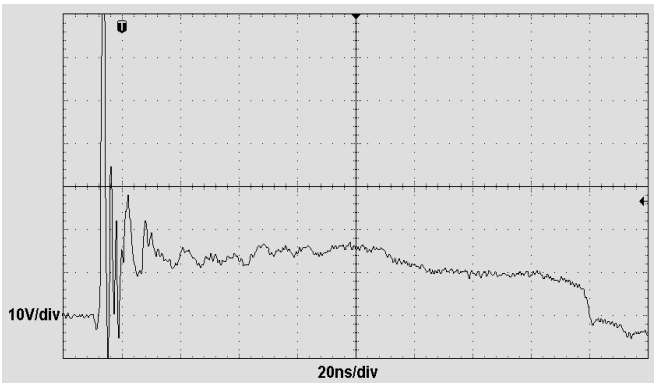
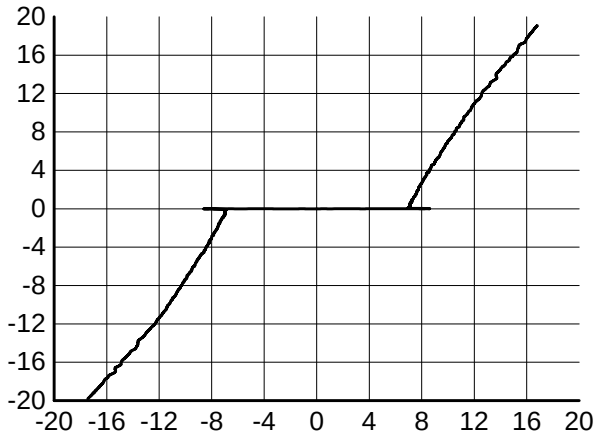
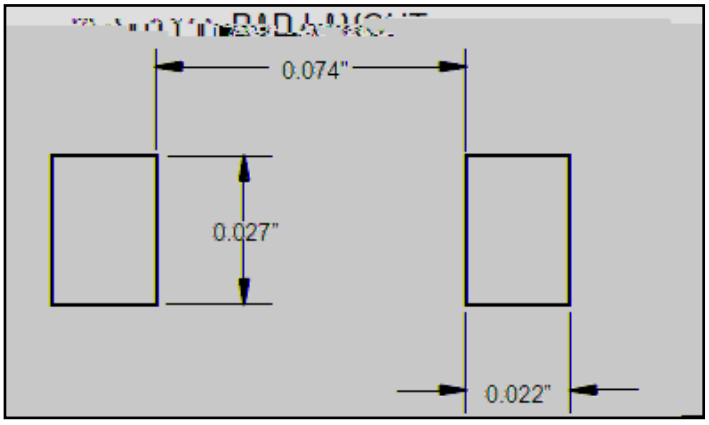

10V/div
20ns/div


20
16
12
8
4
0
-4
-8
-12
-16
-20
-20 -16 -12 -8 -4 0 4 8 12 16 20

1.000	A	
0.100	A1	0.000
0.900	A2	0.800
0.400	b	0.250
2.700	E1	2.500
0	0°	8°

■



Unit inches